

Amendments to the Specification:

On page 7, line 20, please replace the current paragraph with the following new paragraph:

Referring again to Fig. 2, after device fabrication (completion of Step S6), the piezoelectric layer 210 is subjected to a selective etching process, i.e., a “trenching” process (Step S7). One such trenching process is described in co-pending U.S. Patent Application Serial No. 09/XXX,XXX497,982, now U.S. Patent No.: 6,306,313, entitled “Selective Etching of Thin Films”, ~~which is commonly assigned and concurrently filed with the present application.~~ Specifically, any piezoelectric material not involved in signal transmission (not between the electrodes 205 and 215) is removed by chemical etching. This etching can be accomplished by wet etching, ion beam milling, or preferably in a reactive ion etch (RIE) chamber employing chlorine chemistry and plasma bombardment to remove material. Again photo-definable resist is used to preserve the regions between electrodes 205 and 215 that should not be etched. Thus, propagation of lateral acoustic modes is limited to the un-etched regions of the device, inhibiting cross-device interference and energy loss.